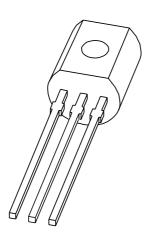
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS8550 PNP medium power 25 V transistor

Product specification Supersedes data of 2002 Nov 19 2004 Aug 10





PNP medium power 25 V transistor

PSS8550

FEATURES

- · High total power dissipation
- · High current capability.

APPLICATIONS

- · Medium power switching and muting
- Amplification
- Portable radio output amplifier (class-B, push-pull).

DESCRIPTION

PNP transistor in a SOT54 (TO-92) plastic package. NPN complement: PSS8050.

MARKING

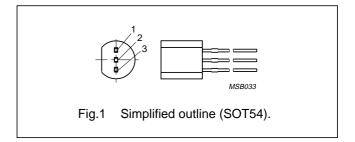
TYPE NUMBER	MARKING CODE
PSS8550C	S8550C
PSS8550D	S8550D

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-25	V
I _C	collector current (DC)	-1.5	А

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V _{CEO}	collector-emitter voltage	open base	_	-25	V
V _{EBO}	emitter-base voltage	open collector	_	-6	V
Ic	collector current (DC)		_	-1.5	Α
I _{CM}	peak collector current		_	-2	Α
I _B	base current (DC)		_	-300	mA
I _{BM}	peak base current		_	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	850	mW
		T _{amb} ≤ 25 °C; note 2	_	900	mW
		T _{amb} ≤ 25 °C; note 3	_	1	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint. Operated under pulsed conditions: pulse width $t_p \le 1$ s; duty cycle $\delta \le 0.75\%$.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	147	K/W
		in free air; note 2	139	K/W
		in free air; note 3	125	K/W

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint. Operated under pulsed conditions: pulse width $t_p \le 1$ s; duty cycle $\delta \le 0.75\%$.

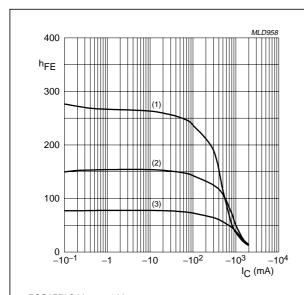
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -35 \text{ V}; I_E = 0$	_	_	-100	nA
		$V_{CB} = -35 \text{ V}; I_E = 0;$ $T_{amb} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -25 \text{ V}; I_B = 0$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -5 \text{ mA}; V_{CE} = -1 \text{ V}$	45	_	_	
		$I_C = -800 \text{ mA}; V_{CE} = -1 \text{ V}$	40	_	_	
	DC current gain	$I_C = -100 \text{ mA}; V_{CE} = -1 \text{ V}$				
	PSS8550C		120	-	200	
	PSS8550D		160	-	300	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -800 \text{ mA}; I_B = -80 \text{ mA}$	_	-190	-500	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -800 \text{ mA}; I_B = -80 \text{ mA}$	_	_	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$I_C = -10 \text{ mA}; V_{CE} = -1 \text{ V}$	_	_	-1	V
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz	100	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	_	12	pF

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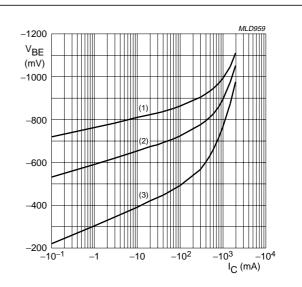
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 $\textbf{PSS8550C} \ \ V_{CE} = -1 \ \ V.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

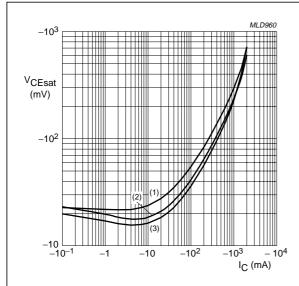
Fig.2 DC current gain as a function of collector current; typical values.



 $\textbf{PSS8550C} \ \ V_{CE} = -1 \ \ V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

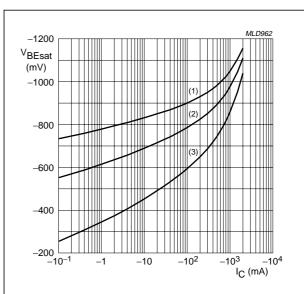
Fig.3 Base-emitter voltage as a function of collector current; typical values.



PSS8550C $I_C/I_B = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



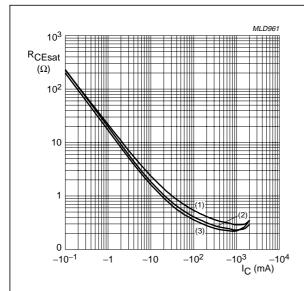
PSS8550C $I_{\text{C}}/I_{\text{B}} = 10$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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PSS8550C $I_{C}/I_{B} = 10$.

- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.

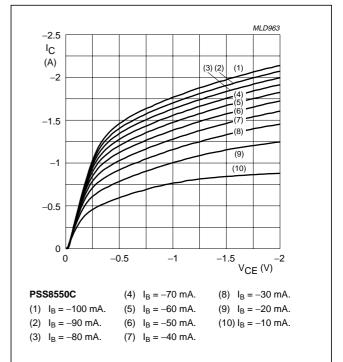
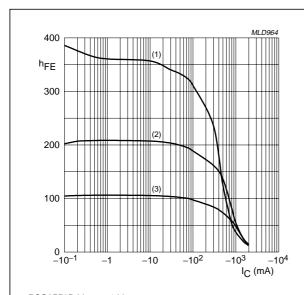


Fig.7 Collector current as a function of collector-emitter voltage; typical values.

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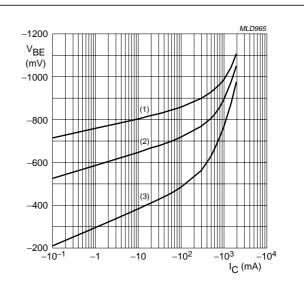
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 $\textbf{PSS8550D} \ V_{CE} = -1 \ V.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

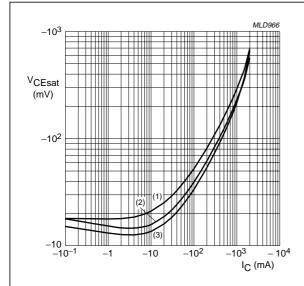
Fig.8 DC current gain as a function of collector current; typical values.



 $\textbf{PSS8550D} \ V_{CE} = -1 \ V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

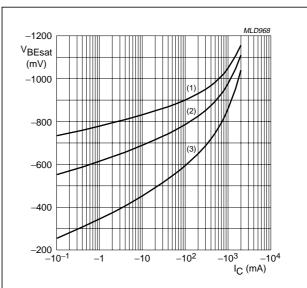
Fig.9 Base-emitter voltage as a function of collector current; typical values.



PSS8550D $I_C/I_B = 10$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.10 Collector-emitter saturation voltage as a function of collector current; typical values.



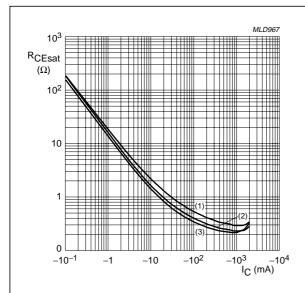
PSS8550D $I_{\text{C}}/I_{\text{B}} = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.11 Base-emitter saturation voltage as a function of collector current; typical values.

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PSS8550D $I_{\text{C}}/I_{\text{B}} = 10.$

- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.12 Equivalent on-resistance as a function of collector current; typical values.

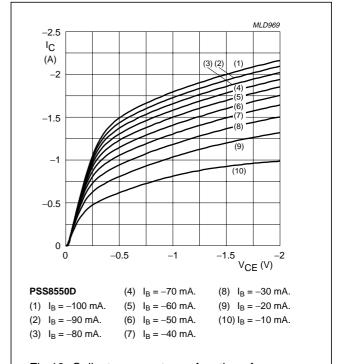


Fig.13 Collector current as a function of collector-emitter voltage; typical values.

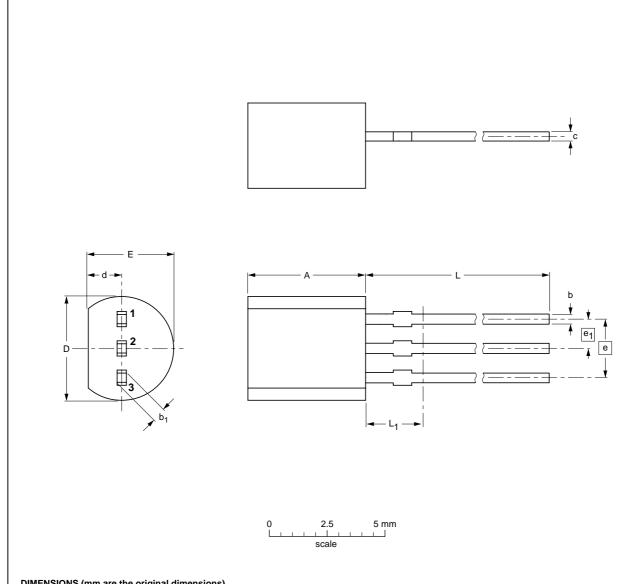
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION IEC		JEDEC	JEITA		PROJECTION	1330E DATE
SOT54		TO-92	SC-43A			97-02-28 04-06-28

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LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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Printed in The Netherlands

R75/02/pp10

Date of release: 2004 Aug 10

Document order number: 9397 750 13683

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